# LOW VOLTAGE EEPROM/NVRAM TRANSISTORS AND MAKING METHOD

## ABSTRACT OF THE DISCLOSURE

An electrically programmable memory device which has greater efficiency of electron injection from the channel to the floating gate comprising a substrate having source and drain regions with a channel therebetween; a floating gate structure over portions of said source and drain regions and said channel, which structure includes a dielectric layer and a conductor layer thereover; and said channel under said floating gate having both horizontal and vertical components. The present invention also relates to a method for fabricating said memory device.

**(FIGURE 4 IS SUGGESTED FOR PUBLICATION)**